



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: MINETANI, Keiji

Serial No.: 09/893,477

Filed: June 29, 2001

Corres. and Mail

BOX AF

Group Art Unit: 2822

Examiner: LEWIS, Monica

P.T.O. Confirmation No.: 5295

For: **COMPOUND SEMICONDUCTOR DEVICE HAVING
A MESFET THAT RAISES THE MAXIMUM
MUTUAL CONDUCTANCE AND CHANGES THE
MUTUAL CONDUCTANCE**

RESPONSE UNDER 37 CFR §1.116

- EXPEDITED RESPONSE -

GROUP ART UNIT 2822

BOX AF

Commissioner for Patents
Washington, D.C. 20231

December 10, 2002

Sir:

In response to the Office Action dated September 10, 2002, please amend the above-identified application as follows:

IN THE CLAIMS

Please amend claim 1 to read as follows:

- 506 B1
C1
1. (Twice amended) A compound semiconductor device comprising:
a substrate formed of a first compound semiconductor;
a buffer layer formed on the substrate;
a graded channel layer formed on the buffer layer, and formed of a second compound